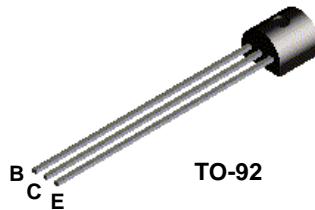


## BC368



### NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.5 A. Sourced from Process 37.

#### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	20	V
V <sub>CES</sub>	Collector-Base Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	2.0	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

#### Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BC368	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625	mW
		5.0	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

# NPN General Purpose Amplifier

(continued)

BC368

## Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emmitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	20		V
$V_{(BR)CES}$	Collector-Base Breakdown Voltage	$I_C = 100 \text{ } \mu\text{A}, I_E = 0$	25		V
$V_{(BR)EBO}$	Emmitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	5.0		V
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$		10 1.0	$\mu\text{A}$ mA
$I_{EBO}$	Emmitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		10	$\mu\text{A}$

### ON CHARACTERISTICS

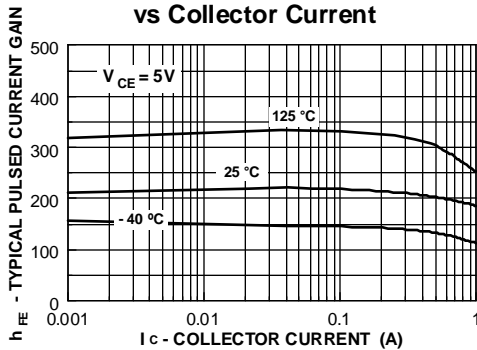
$h_{FE}$	DC Current Gain	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 0.5 \text{ A}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$	50 85 60	375	
$V_{CE(sat)}$	Collector-Emmitter Saturation Voltage	$I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$		0.5	V
$V_{BE(on)}$	Base-Emmitter On Voltage	$I_C = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$		1.0	V

### SMALL SIGNAL CHARACTERISTICS

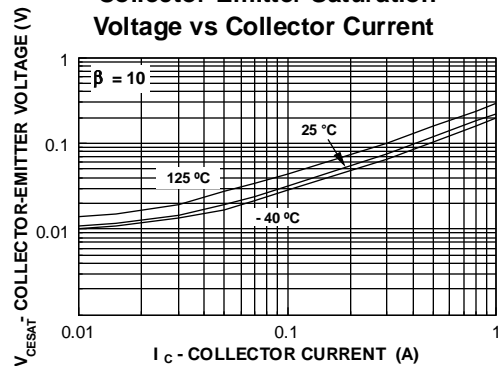
$f_T$	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 35 \text{ MHz}$	45		MHz
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## Typical Characteristics

Typical Pulsed Current Gain vs Collector Current

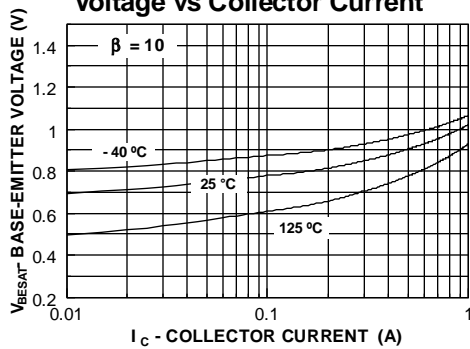


Collector-Emmitter Saturation Voltage vs Collector Current

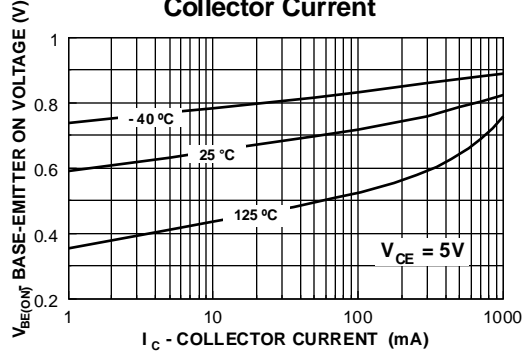


Typical Characteristics (continued)

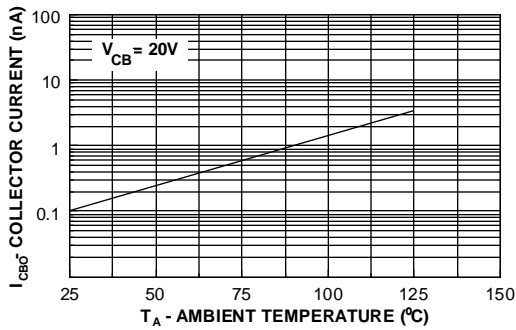
Base-Emitter Saturation Voltage vs Collector Current



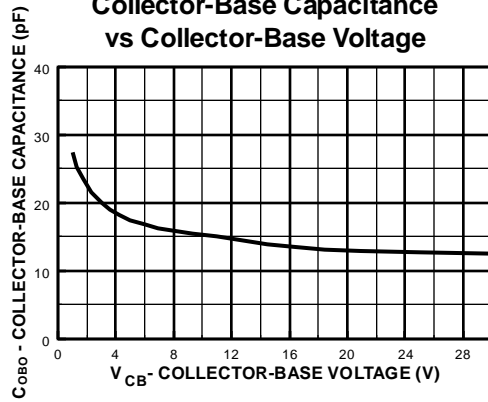
Base-Emitter ON Voltage vs Collector Current



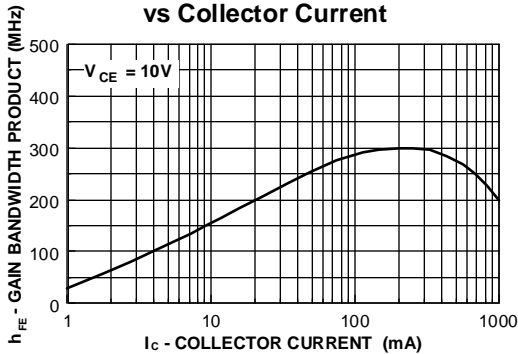
Collector-Cutoff Current vs Ambient Temperature



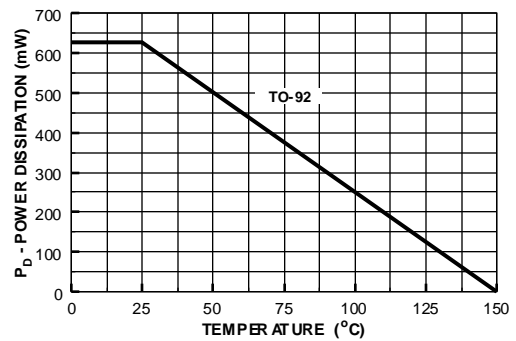
Collector-Base Capacitance vs Collector-Base Voltage



Gain Bandwidth Product vs Collector Current



Power Dissipation vs Ambient Temperature



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## PRODUCT STATUS DEFINITIONS

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